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ABSTRACT OF THE DISCLOSURE

A semiconductor wafer made from silicon which is doped with hydrogen. The hydrogen concentration is less than $5 \cdot 10^{16}$ atcm⁻³ and greater than $1 \cdot 10^{12}$ atcm⁻³. A method for producing a semiconductor wafer from silicon includes separating the semiconductor wafer from a silicon single crystal, with the single silicon crystal being pulled from a melt, in the presence of hydrogen, using the Czochralski method. The hydrogen partial pressure during the pulling of the single silicon crystal is less than 3 mbar.